

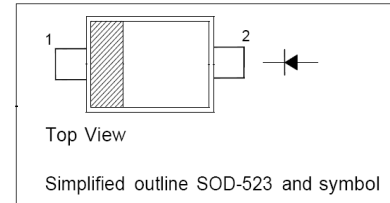
Surface Mount Schottky Barrier Diodes

Features

- Low Forward Voltage

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V _{RRM}	40	V
Reverse Voltage	V _R	40	V
Average Forward Rectified Current	I _{F(AV)}	250	mA
Non-Repetitive Peak Forward Surge Current at t = 1 s	I _{FSM}	2	A
Power Dissipation	P _{tot}	200	mW
Operating and Storage Temperature Range	T _J , T _{stg}	- 65 to + 125	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage at I _R = 10 μA	V _{(BR)R}	40	-	-	V
Reverse Leakage Current at V _R = 30 V at V _R = 20 V at V _R = 10 V	I _R	-	-	5	μA
Forward Voltage at I _F = 20 mA at I _F = 200 mA	V _F	-	-	0.37 0.6	V
Total Capacitance at V _R = 0 V, f = 1 MHz	C _T	-	50	-	pF
Reverse Recovery Time at I _F = I _R = 200 mA, I _{rr} = 0.1 I _R , R _L = 100 Ω	t _{rr}	-	10	-	ns

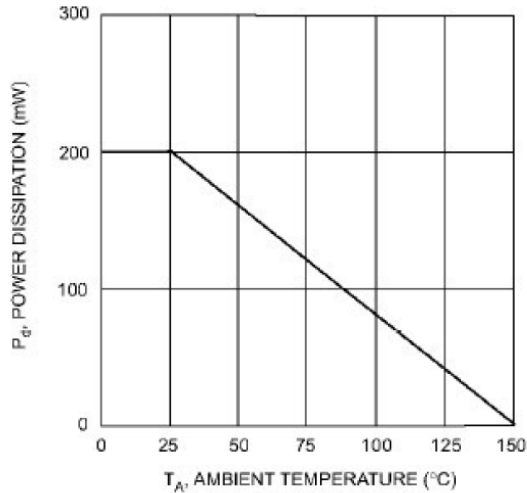


Fig. 1 Power Derating Curve

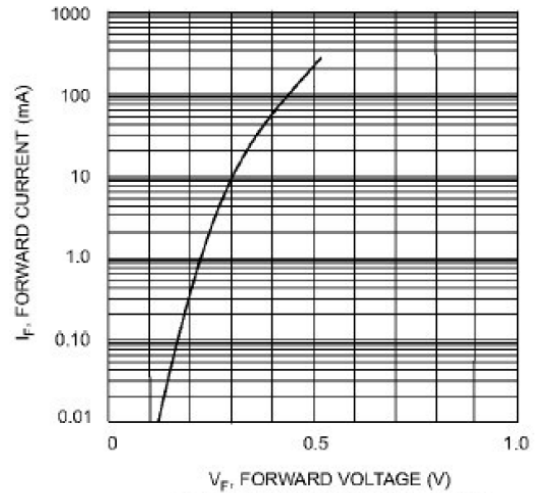


Fig. 2 Typical Forward Characteristics

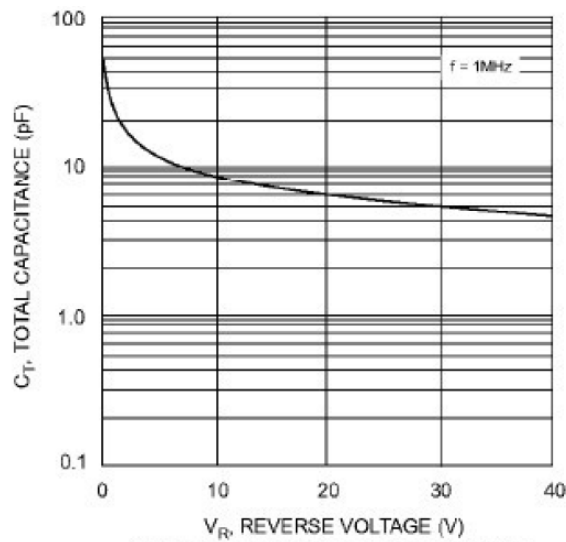
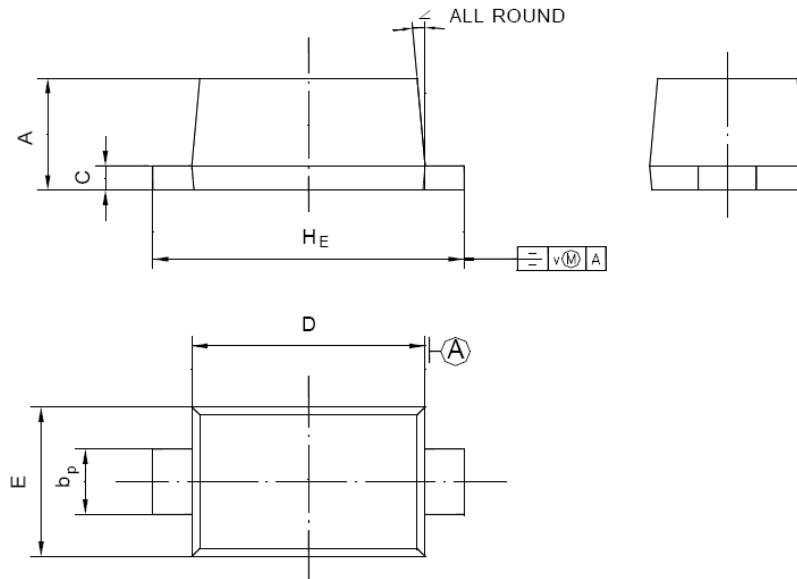


Fig. 3 Total Capacitance vs Reverse Voltage

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads SOD-523



UNIT	A	b _p	C	D	E	H _E	V	∠
mm	0.70 0.60	0.4 0.3	0.135 0.100	1.25 1.15	0.85 0.75	1.7 1.5	0.1	5°

单击下面可查看定价，库存，交付和生命周期等信息

[>>SHIKUES\(时科\)](#)